

GM1188

PNP SILICON EPITAXIAL TRANSISTOR

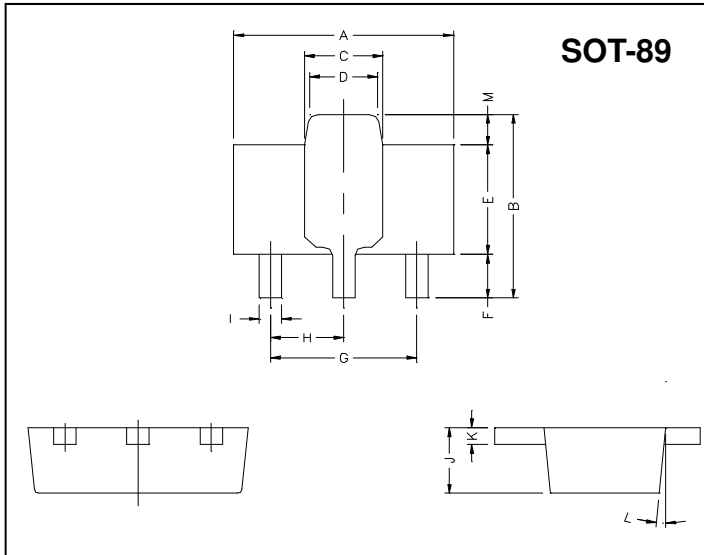
Description

The GM1188 is designed for medium power amplifier applications.

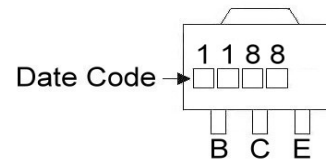
Features

- Low collector saturation voltage : $V_{CE(sat)} = -0.5V$ (Typ.)
- Complementary pair with GM1766

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55~+150	$^\circ C$
Collector to Base Voltage	V_{CB0}	-40	V
Collector to Emitter Voltage	V_{CE0}	-32	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-2	A
Total Power Dissipation	P_D	0.5 (2.0*)	W

*When mounted on a 40x40x0.7mm ceramic board.

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise noted)

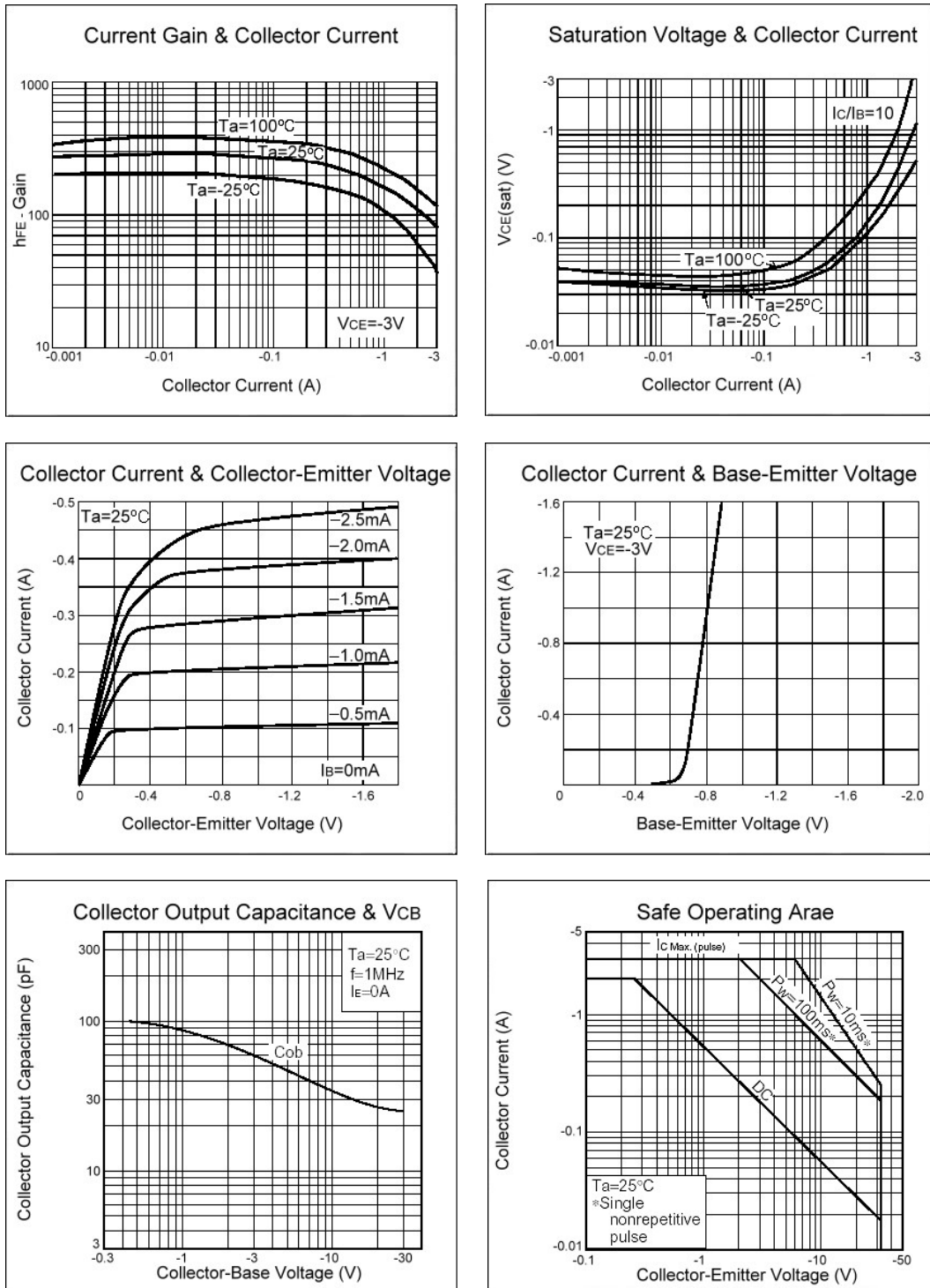
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CB0}	-40	-	-	V	$I_C = -50\mu A, I_E = 0$
V_{CE0}	-32	-	-	V	$I_C = -1mA, I_B = 0$
V_{EB0}	-5	-	-	V	$I_E = -50\mu A, I_C = 0$
I_{CB0}	-	-	-1	μA	$V_{CB} = -20V, I_E = 0$
I_{EB0}	-	-	-1	μA	$V_{EB} = -4V, I_C = 0$
* $V_{CE(sat)}$	-	-500	-800	mV	$I_C = -2A, I_B = -200mA$
* h_{FE}	82	-	390		$V_{CE} = -3V, I_C = -500mA$
f_T	-	150	-	MHz	$V_{CE} = -5V, I_C = -500mA, f = 30MHz$
C_{ob}	-	50	-	pF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	P	Q	R
Range	82 ~ 180	120 ~ 270	180 ~ 390

Characteristics Curve



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